

N-Channel 90 V (D-S) MOSFET

PRODUCT SUMMARY	
V_{DS} (V)	90
$R_{DS(on)}$ (Ω) at $V_{GS} = 10$ V	4
Configuration	Single

FEATURES

- Military Qualified
- Low On-Resistance: 3.6Ω
- Low Threshold: 1.6 V
- Low Input Capacitance: 35 pF
- Fast Switching Speed: 6 ns
- Low Input and Output Leakage

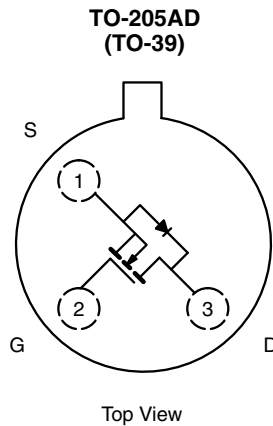


BENEFITS

- Guaranteed Reliability
- Low Offset Voltage
- Low-Voltage Operation
- Easily Driven Without Buffer
- High-Speed Circuits
- Low Error Voltage

APPLICATIONS

- Hi-Rel Systems
- Direct Logic-Level Interface: TTL/CMOS
- Drivers: Relays, Solenoids, Lamps, Hammers, Displays, Memories, Transistors, etc.
- Battery Operated Systems
- Solid-State Relays



ORDERING INFORMATION			
PART	PACKAGE	DESCRIPTION/DSCC PART NUMBER	VISHAY ORDERING PART NUMBER
2N6661	TO-205AD (TO-39)	Commercial	2N6661
2N6661-2		Commercial, Lead (Pb)-free	2N6661-E3
2N6661JANTX		See -2 Flow Document	2N6661-2
2N6661JANTXV		JANTX2N6661 (std Au leads)	2N6661JTX02
		JANTX2N6661 (with solder)	2N6661JTXL02
		JANTX2N6661P (with PIND)	2N6661JTXP02
		JANTXV2N6661 (std Au leads)	2N6661JTXV02
		JANTXV2N6661P (with PIND)	2N6661JTV02

ABSOLUTE MAXIMUM RATINGS ($T_A = 25^\circ\text{C}$, unless otherwise noted)				
PARAMETER		SYMBOL	LIMIT	UNIT
Drain-Source Voltage		V_{DS}	90	V
Gate-Source Voltage		V_{GS}	± 20	
Continuous Drain Current ($T_J = 150^\circ\text{C}$)	$T_C = 25^\circ\text{C}$	I_D	0.86	A
	$T_C = 100^\circ\text{C}$		0.54	
Pulsed Drain Current ^a		I_{DM}	3	
Maximum Power Dissipation	$T_C = 25^\circ\text{C}$	P_D	6.25	W
	$T_A = 25^\circ\text{C}$		0.725	
Thermal Resistance, Junction-to-Ambient ^b		R_{thJA}	170	$^\circ\text{C/W}$
Thermal Resistance, Junction-to-Case		R_{thJC}	20	
Operating Junction and Storage Temperature Range		T_J, T_{stg}	- 55 to 150	$^\circ\text{C}$

Notes

- Pulse width limited by maximum junction temperature.
- Not required by military spec.



SPECIFICATIONS (T _A = 25 °C, unless otherwise noted)									
PARAMETER	SYMBOL	TEST CONDITIONS	LIMITS			UNIT			
			MIN.	TYP. ^b	MAX.				
Static									
Drain-Source Breakdown Voltage	V _{DS}	V _{DS} = 0 V, I _D = 10 μA	90	125	-	V			
Gate-Source Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 1 mA	0.8	1.6	2				
			T _A = -55 °C	-	1.8		2.5		
			T _A = 125 °C	0.3	1.3	-			
Gate-Body Leakage	I _{GSS}	V _{GS} = ±20 V	V _{DS} = 0 V	-	-	±100	nA		
			T _A = 125 °C	-	-	±500			
Zero Gate Voltage Drain Current	I _{DSS}	V _{GS} = 0 V	V _{DS} = 72 V	-	-	1	μA		
			T _A = 125 °C	-	-	100			
On-State Drain Current ^b	I _{D(on)}	V _{GS} = 10 V	V _{DS} = 10 V	-	1.8	-	mA		
Drain-Source On-State Resistance ^b	R _{DS(on)}	V _{GS} = 5 V	I _D = 0.3 A	-	3.8	5.3	Ω		
				V _{GS} = 10 V	I _D = 1 A	-		3.6	4
						T _A = 125 °C ^d		-	6.7
Forward Transconductance ^b	g _{fs}	V _{DS} = 7.5 V, I _D = 0.475 A		170	340	-	mS		
Diode Forward Voltage	V _{SD}	V _{GS} = 0 V	I _S = 0.86 A	0.7	0.9	1.4	V		
Dynamic									
Input Capacitance	C _{iss}	V _{GS} = 0 V	V _{DS} = 25 V, f = 1 MHz	-	35	50	pF		
Output Capacitance	C _{oss}			-	15	40			
Reverse Transfer Capacitance	C _{rss}			-	2	10			
Drain-Source Capacitance	C _{ds}			-	30	-			
Switching^c									
Turn-On Time	t _{ON}	V _{DD} = 25 V, R _L = 23 Ω		-	6	10	ns		
Turn-Off Time	t _{OFF}	I _D ≅ 1 A, V _{GEN} = 10 V, R _g = 23 Ω		-	8	10			

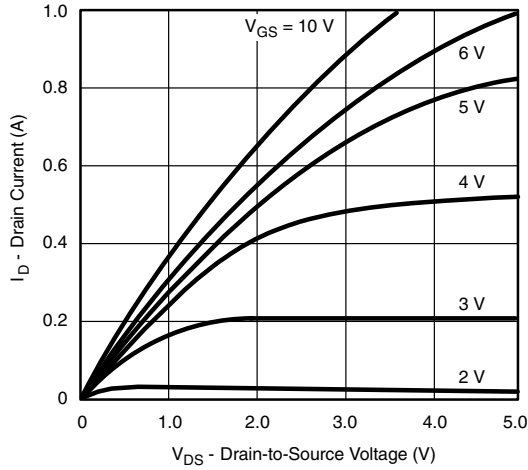
Notes

- a. FOR DESIGN AID ONLY, not subject to production testing.
- b. Pulse test: PW ≤ 300 μs duty cycle ≤ 2 %.
- c. Switching time is essentially independent of operating temperature.
- d. This parameter not registered with JEDEC.

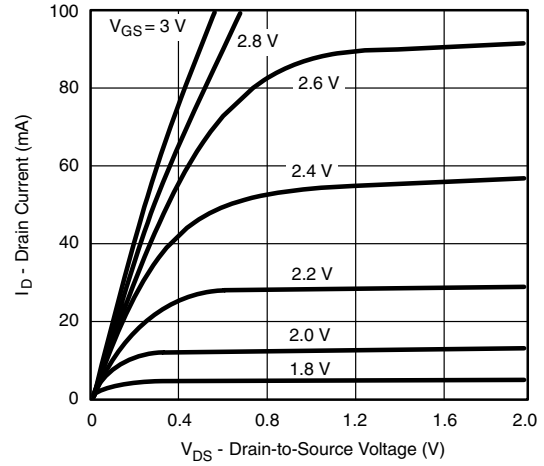
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



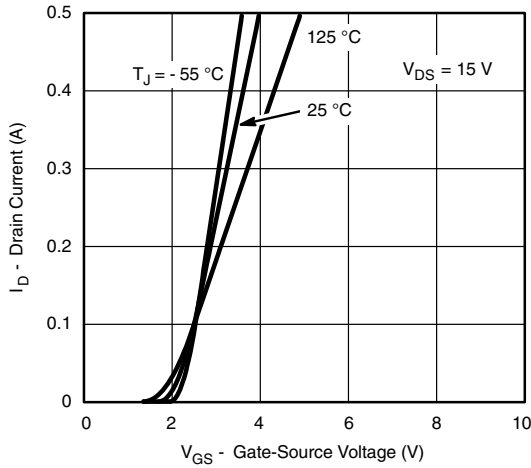
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



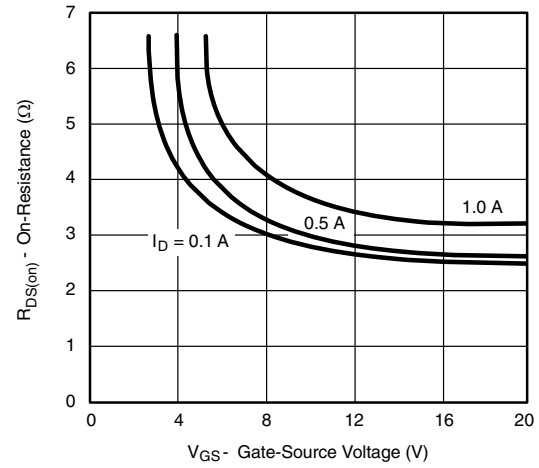
Ohmic Region Characteristics



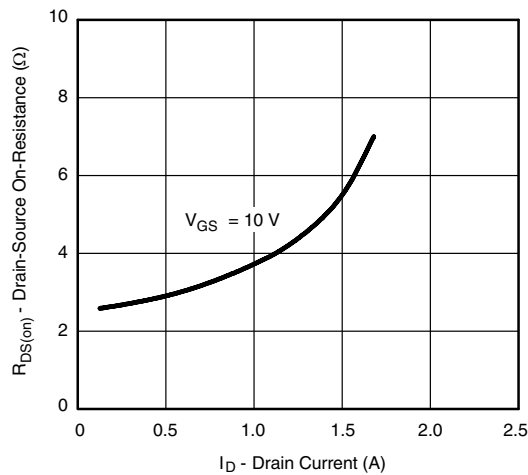
Output Characteristics for Low Gate Drive



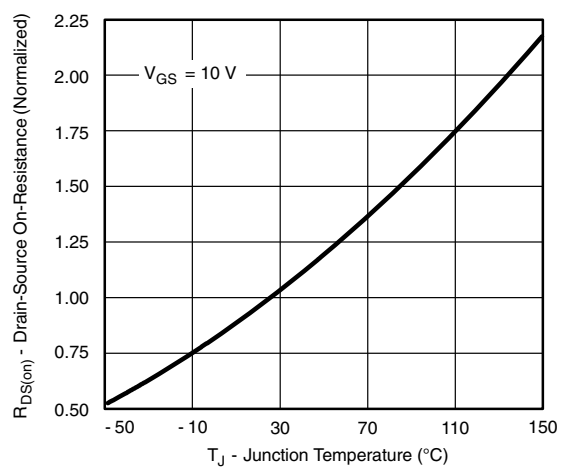
Transfer Characteristics



On-Resistance vs. Gate-to-Source Voltage



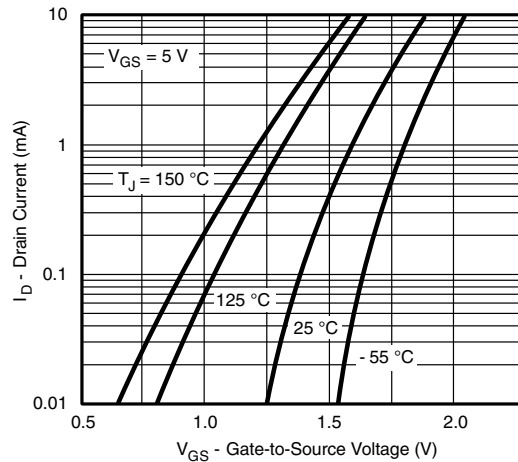
On-Resistance vs. Drain Current



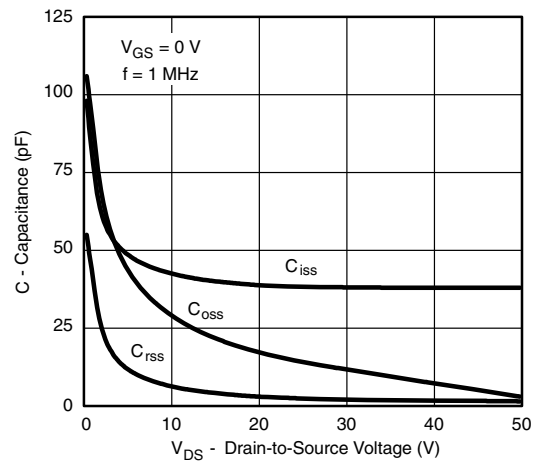
Normalized On-Resistance vs. Junction Temperature



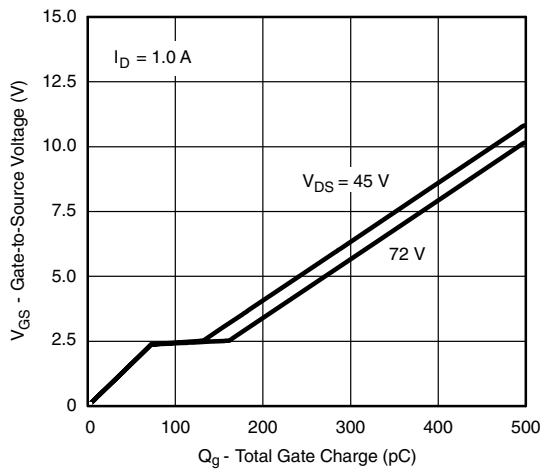
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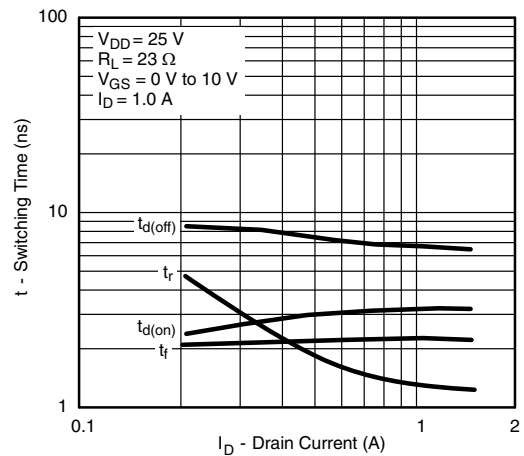
Threshold Region



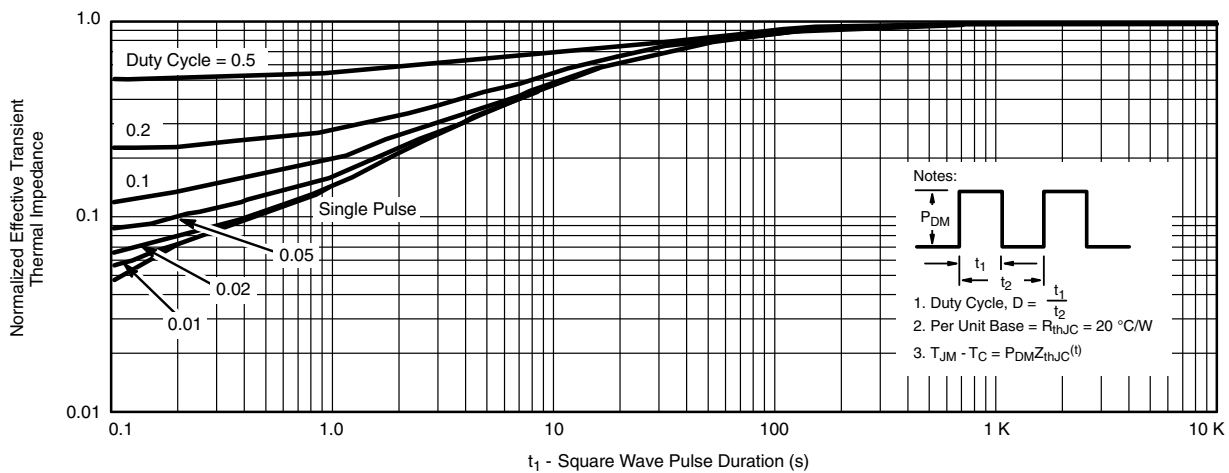
Capacitance



Gate Charge



Load Condition Effects on Switching



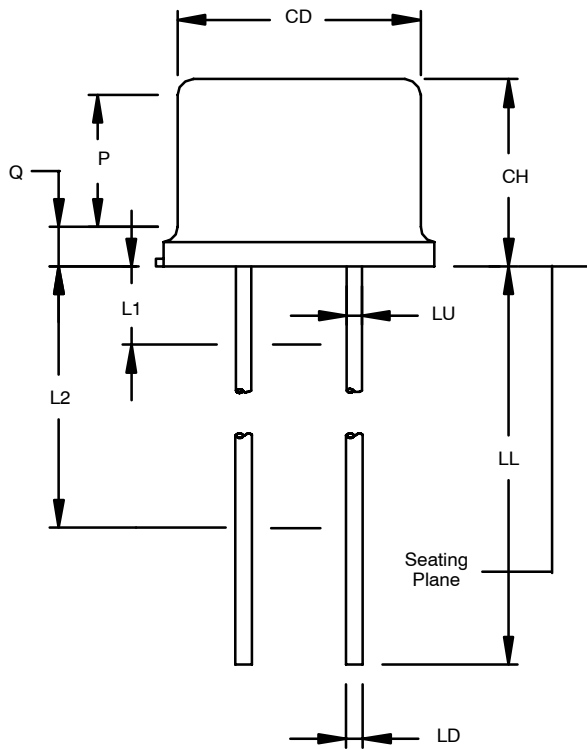
Normalized Thermal Transient Impedance, Junction-to-Ambient

Notes:

 1. Duty Cycle, $D = \frac{t_1}{t_2}$
 2. Per Unit Base = $R_{thJC} = 20\text{ }^\circ\text{C/W}$
 3. $T_{JM} - T_C = P_{DM}Z_{thJC}(t)$

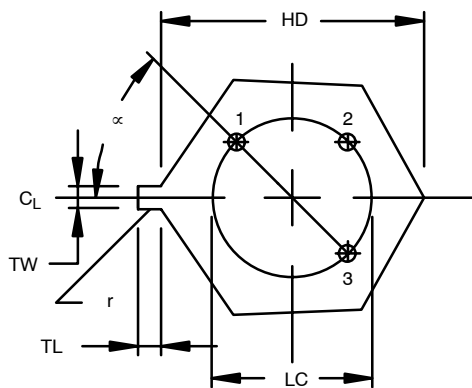
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TO-205AD (TO-39 TALL LID)



Dim	INCHES		MILLIMETERS		Notes
	Min	Max	Min	Max	
CD	0.305	0.335	7.75	8.51	
CH	0.240	0.260	6.10	6.60	
HD	0.335	0.370	8.51	9.40	
LC	0.200 TP		5.08 TP		6
LD	0.016	0.021	0.41	0.53	7, 8
LL	0.500	0.750	12.70	19.05	7, 8
LU	0.016	0.019	0.41	0.48	7, 8
L1	—	0.050	—	1.27	7, 8
L2	0.250	—	6.35	—	7, 8
P	0.100	—	2.54	—	5
Q	—	0.050	—	1.27	4
r	—	0.010	—	0.25	9
TL	0.029	0.045	0.74	1.14	3
TW	0.028	0.034	0.71	0.86	2
α	45° TP		45° TP		6

Dimensions (see notes 1, 2, 9, 11, 12)
 ECN: S-40373—Rev. C, 15-Mar-04
 DWG: 5511



NOTES:

- Dimensions are in inches. Metric equivalents are given for general information only.
- Beyond radius (r) maximum, TW shall be held for a minimum length of 0.011 (0.028 mm).
- Dimension TL measured from maximum HD.
- Outline in this zone is not controlled.
- Dimension CD shall not vary more than 0.010 (0.25 mm) in zone P. This zone is controlled for automatic handling.
- Leads at gauge plane $0.054+0.001, -0.000$ ($1.37+0.03, -0.00$ mm) below seating plane shall be within 0.007 (0.18 mm) radius of true position (TP) at maximum material condition (MMC) relative to tab at MMC.
- LU applies between L1 and L2, LD applies between L2 and L maximum. Diameter is uncontrolled in L1 and beyond LL minimum.
- All three leads.
- Radius (r) applies to both inside corners of tab.
- Drain is electrically connected to the case.



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